

Supporting information:

Synergistically optimized electrical and thermal transport properties in SnTe *via* alloying high-solubility MnTe

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Table S1. Densities (d , g/cm³) of all samples Sn_{1-x}Mn_xTe ($x=0$, 1%, 3%, 5%, 7%, 9%, 11%, 13%, 15%, 17%, 19%, 20%, 25% and 50%, in mole ratio) investigated in this study.

x	0	1%	3%	5%	7%	9%	11%	13%	15%	17%	19%	20%	25%	50%
d	6.26	6.274	6.212	6.161	5.819	6.075	5.953	5.943	5.63	5.86	5.805	5.811	6.126	5.763

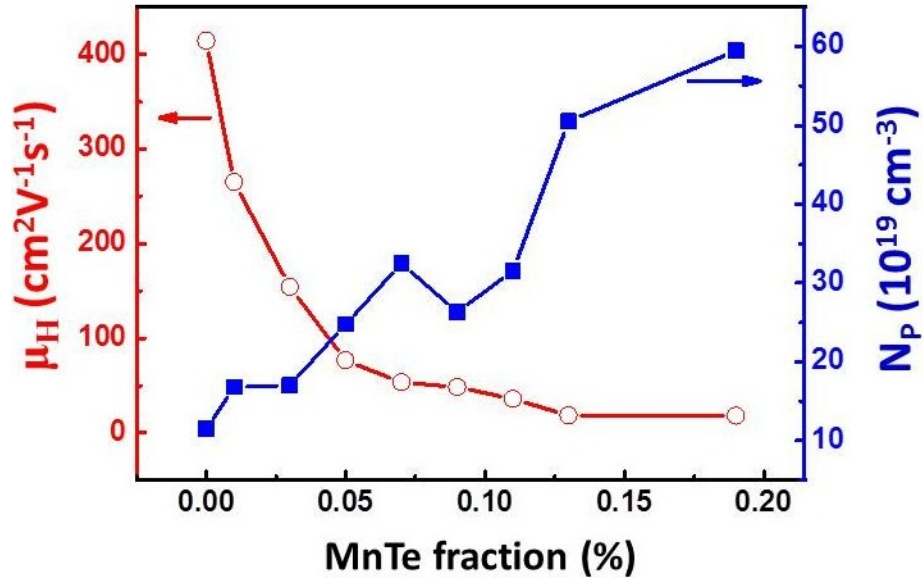


Figure S1. Carrier concentration and mobility in SnTe sample as a function of alloying MnTe fraction at room temperature.

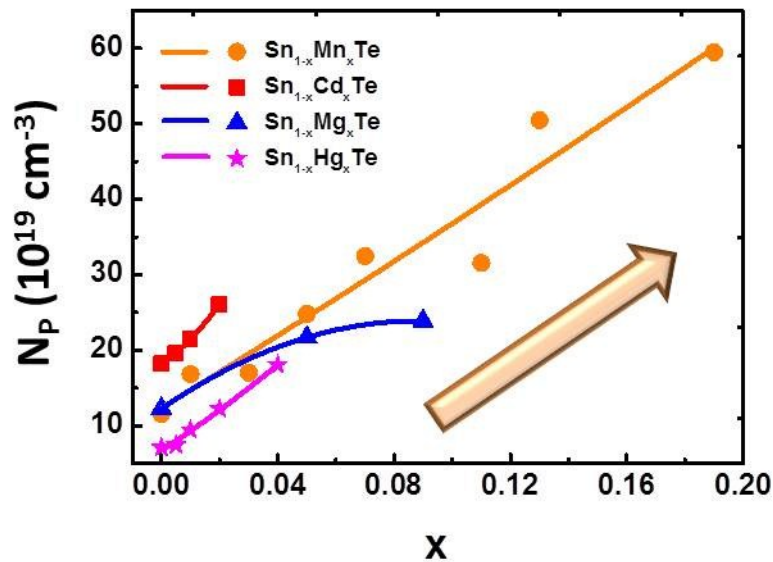


Figure S2. Room temperature hole concentration (N_p) as a function of Mn, Cd, Mg and Hg fraction alloying in SnTe.

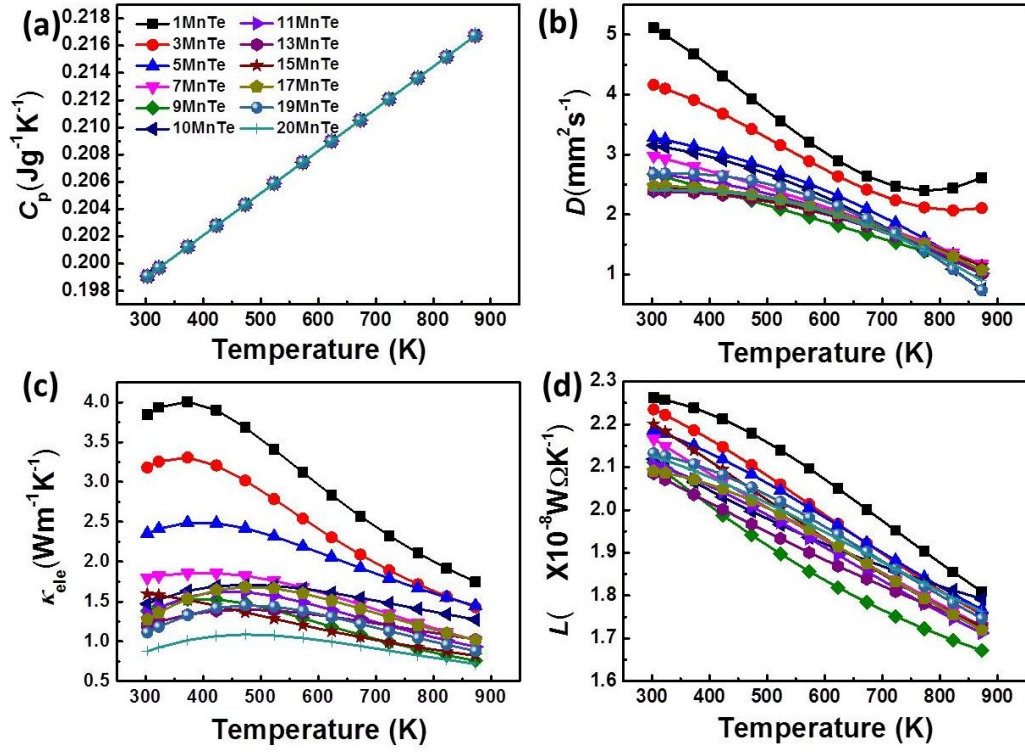


Figure S3. Temperature dependent (a) Heat capacity C_p , (b) thermal diffusivity D , (c) electronic thermal conductivity, (d) Calculated Lorenz number L for $\text{Sn}_{1-x}\text{Mn}_x\text{Te}$.

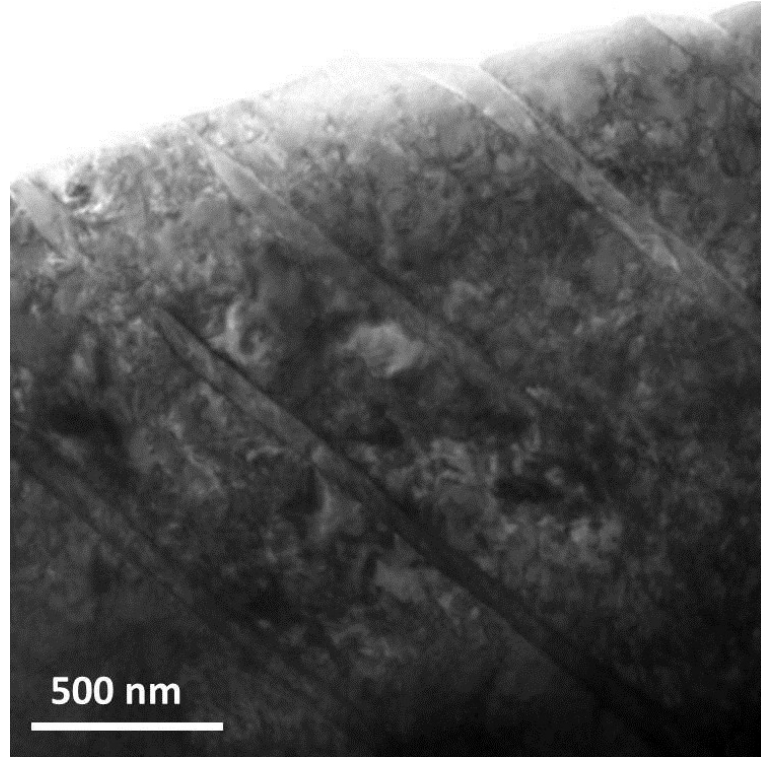


Figure S4. Medium-magnification TEM image of SnTe alloyed with 19% MnTe .